

Silicon Bridge Rectifier

 $V_{RRM} = 50\text{ V} - 1000\text{ V}$
 $I_F = 2\text{ A}$

Features

- Types up to 1000 V V_{RRM}
- Ideal for printed circuit board
- Built-in printed circuit board stand-offs
- High temperature soldering guaranteed 265°C/ 10 seconds
- High case dielectric strength
- Plastic package has Underwriters Laboratory Flammability Classification 94V-0

KBP Package


Mechanical Data

Case: Reliable low cost construction

Weight: 0.065 oz, 2.2 g

Mounting position: Any

Terminals: Plated leads, solderable per MIL-STD-202, Method 208

Maximum ratings, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	KBP206	KBP208	KBP210	Unit
Repetitive peak reverse voltage	V_{RRM}		600	800	1000	V
RMS reverse voltage	V_{RMS}		420	560	700	V
DC blocking voltage	V_{DC}		600	800	1000	V
Continuous forward current	I_F	$T_C \leq 50\text{ °C}$	2	2	2	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$, $t_p = 8.3\text{ ms}$	60	60	60	A
Operating temperature	T_j		-50 to 150	-50 to 150	-50 to 150	°C
Storage temperature	T_{stg}		-50 to 150	-50 to 150	-50 to 150	°C

Electrical characteristics, at $T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	KBP206	KBP208	KBP210	Unit
Diode forward voltage	V_F	$I_F = 2\text{ A}$, $T_j = 25\text{ °C}$	1.1	1.1	1.1	V
Reverse current	I_R	$V_R = 50\text{ V}$, $T_j = 25\text{ °C}$ $V_R = 50\text{ V}$, $T_j = 100\text{ °C}$	10 200	10 200	10 200	μA

Thermal characteristics

Parameter	Symbol	Conditions	KBP206	KBP208	KBP210	Unit
Thermal resistance, junction - case	R_{thJL}		25.0	25.0	25.0	°C/W

